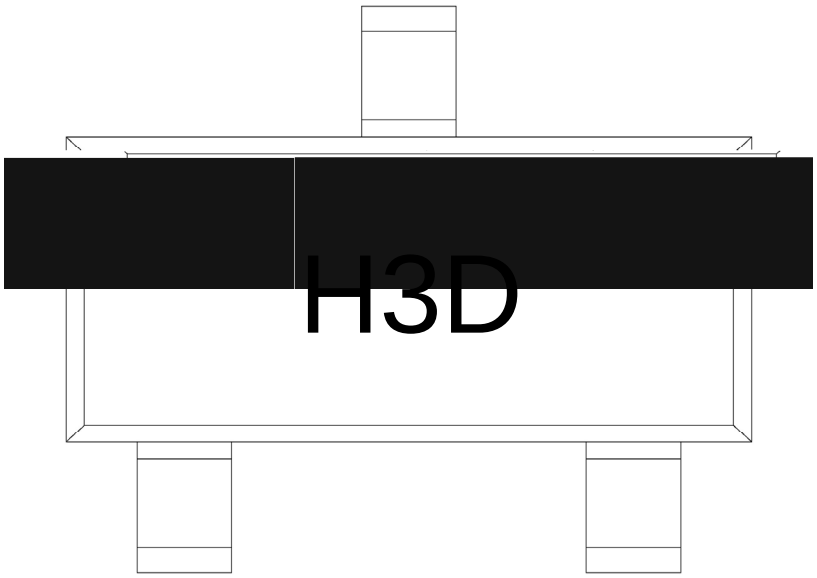
/ Absolute Maximum Ratings(Ta=25)

v Ѽ Parameter	ч N Symbol	Ѽ Ё Rating	D Ц Unit
Collector to Base Voltage	V_{CBO}	500	V
Collector to Emitter Voltage	V_{CEO}	400	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	300	mA
Collector Power Dissipation	P_C	350	mW
Collector Power Dissipation	$P_{C(TC=25\ )}$	1.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

v Ѽ Parameter	ч N Symbol	Ш : ↑ Ч Test Conditions	ѡ ѻ Ё Min	Ɛ ʒ Ё Typ	ѡ ᶻ Ё Max	D Ц Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_E=0	500			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	400			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=10μA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=400V I_E=0			0.1	μA
Collector Cut-Off Current	I_{CES}	V_{CE}=400V V_{BE}=0			1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=4.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=10V I_C=10mA	50		200	
	$h_{FE(2)}$	V_{CE}=10V I_C=100mA	40			
	$h_{FE(3)}$	V_{CE}=10V I_C=50mA	45			
	$h_{FE(4)}$	V_{CE}=10V I_C=1.0mA	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=1.0mA I_B=0.1mA			0.4	V
	$V_{CE(sat)(2)}$	I_C=10mA I_B=1.0mA			0.5	V
	$V_{CE(sat)(3)}$	I_C=50mA I_B=5.0mA			0.75	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=10mA I_B=1.0mA			0.75	V
Output Capacitance	C_{ob}	V_{CB}=20V I_E=0 f=1.0MHz			7.0	pF

/ Marking Instructions



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Note:

K χ Company Code

3D χ Product Type Code